Supporting Information

Real-time Observing Ultrafast Carrier and Phonon Dynamics in Colloidal Tin Chalcogenide van der Waals Nanosheets

Xufeng Li¹, Nannan Luo², Yuzhong Chen¹, Xiaolong Zou², Haiming Zhu^{1,3*}

1. Centre for Chemistry of High-Performance & Novel Materials, Department of Chemistry, Zhejiang University, Hangzhou, Zhejiang, 310027, China

2. The Low-Dimensional Materials and Devices Laboratory, Tsinghua-Berkeley Shenzhen Institute, Tsinghua University, Shenzhen, Guangdong 518055, China

3. State Key Laboratory of Modern Optical Instrumentation, Zhejiang University, Hangzhou, Zhejiang, 310027, China.

* Email: hmzhu@zju.edu.cn

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SI1. Morphology control of SnSe2 nanoparticle



Fig. S1. $SnSe_2$ nanoparticle synthesized at different reaction condition. The lateral size of $SnSe_2$ NSs can be controlled by adjusting the radio of Sn and Se precursors. (a) Sn/Se=1/2, lateral size about 50-200 nm. (b) Sn/Se=1/3, lateral size about 200-500 nm. (c) Sn/Se=1/4, lateral size about 1-2 μ m. If no morphology control agent Phen added into reaction system, the product will change to nanoflowers (d). This result is similar to the Li L et al's previous work.¹

SI2. Thickness characterization



Fig. S2. Typical AFM image (a) and the height data (b) of $SnSe_2 NSs$. The morphology of $SnSe_2 NSs$ in AFM image is similar to that in TEM image, and the single sheet which can be easily separated by spin-coating for AFM characterization shows the uniform thickness of ~9 nm.

Electron effective mass /m _e		Hole effective mass /m _e
Γ point:	M point:	
Г-К: 0.1	М-Г: 1.3	Г-К: 1.4
Г-М: 0.1	М-К: 0.6	

Tab. S1 Effective Mass of Carriers in SnSe₂ Band Structure by DFT

SI4. More data of 2.38 eV (520 nm) excitation



Fig. S3. Color plot of TA spectra after 2.38 eV (520 nm) excitation with linear delay time for details of oscillation pattern.



Fig. S4. TA spectra evolution at various pump-probe delays after 2.38 eV excitation.



Fig. S5. Kinetics power-dependence (×10³ mW/cm²) after 2.38 eV (520 nm) excitation. The marks are experimental data and the solid lines are their exponential fits. (a) Decay kinetics of T_2 at different excitation power. (b) Signal intensity of T_2 at different excitation power. (c) Kinetics of T_1 at different excitation power. (d) Generation kinetics of PA at different power. All fitting life times are showed in Table S2.

Signal	Power	Process	life time
T ₂	0.4mW	decay	0.524±0.170ps
	0.8mW	decay	0.427±0.154ps
	1.2mW	decay	0.570±0.363ps
	1.6mW	decay	0.466±0.158ps
	0.4mW	generate	0.217±0.030ps
		decay	2.812±0.212ps
	0.8mW	generate	0.219±0.030ps
т		decay	2.501±0.167ps
11	1.2mW	generate	0.231±0.031ps
		decay	2.492±0.152ps
	1.6mW	generate	0.194?0.030ps
		decay	2.539±0.169ps
PA	0.4mW	generate	2.726±0.166ps
		decay	448.7±10.7ps
	0.8mW	generate	2.686±0.149ps
		decay	501.94±19.1ps
	1.2mW	generate	2.403±0.142ps
		decay	486.35±15.5ps
	1.6mW	generate	2.864±0.35ps
		decay	520.2±20.2ps

Tab. S2 Fitting lifetimes of kinetics after 2.38 eV excitation

SI5. More data of 1.45 eV (850 nm) excitation



Figure S6. Kinetics power-dependence (×10³ mW/cm²) after 1.45 eV (850 nm) excitation. (a) Decay kinetics of T_2 at different excitation power. (b) Signal intensity of T_2 at different excitation power. (c) Decay kinetics of T_1 at different excitation power. (d) Signal intensity of T_1 at different excitation power. (e) Generation kinetics of PA at different excitation power. (f) Decay kinetics of PA at different excitation power. All fitting life times are showed in Table S3.

Signal	Power	Process	life time
B ₂	0.8mW	decay	2.457±0.079ps
	1.6mW	decay	2.391±0.072ps
	2.4mW	decay	2.452±0.071ps
	3.2mW	decay	2.362±0.067ps
B ₁	0.8mW	decay	3.643±0.165ps
	1.6mW	decay	3.415±0.148ps
	2.4mW	decay	3.386±0.142ps
	3.2mW	decay	3.278±0.129ps
А	0.8mW	generate	3.447±0.416ps
		decay	470.61±73.8ps

Tab. S3 Fitting life times of kinetics by 1.45 eV excitation

		1.6mW	generate	3.318±0.402ps
			decay	448.36±30.3ps
		2.4mW	generate	3.198±0.399ps
			decay	391.49±18.6ps
			generate	3.158±0.352ps
	3.2mW	decay	397.46±13.4ps	
			<u>.</u>	

SI6. More data on coherent phonon



Fig. S7. (a) Associated probe energy-resolved Fourier-transformed map of chloroform solvent with oleylamine ligand. A weak solvent response mode can be observed at ~260 cm⁻¹. (b) Associated probe energy-resolved Fourier-transformed map of $SnSe_2 NSs$ by 1.45eV Excitation. (c) Typical kinetics at 1.65 eV with oscillation and exponential fit.

SI7. Experimental details

Chemicals. Tin (IV) chloride pentahydrate (SnCl₄·5H₂O, 98%), Selenium oxide (SeO₂, 99.9%), 1,10-phenanthroline (C₁₂H₈N₂, 99%) and oleylamine (OAM, 70%) were purchased from Sigma-Aldrich. Other common organic solvents (toluene, chloroform and so on, 99.5%) for sample purification and characterization were purchased from Sinopharm Chemical Reagent Co., Ltd. All chemicals were used as received without further purification.

SnSe₂ NSs Synthesis. In a typical synthesis, $SnCl_4 \cdot 5H_2O$ (35mg, 0.1 mmol), 1,10phenanthroline (100 mg, 0.5 mmol), SeO_2 (22 mg, 0.2 mmol) were added into 10 mL OAM (~ 25 mmol) in a 25 mL three-neck flask. With Ar flow, after stirring for 5 min at room temperature, the mixture was heated up to 120°C for 10 min then 200°C for 20 h for reaction. The solution gradually turned dark and the black products were obtained. Varying the precursor ratio of Sn/Se (1:2, 1:3 and 1:4) by changing the amount of SeO₂ (22, 33 and 44 mg) can control the lateral size of SnSe₂ NSs. After reaction, the mixture was cooled down to 50 $^{\circ}$ C, and about 4 times volume of toluene was added. The products were isolated by centrifuge and the precipitates were dispersed in toluene. This purification was repeated twice and the SnSe₂ NSs were finally dispersed in toluene or chloroform.

Characterizations. The SnSe₂ NSs were dropped onto an ultrathin carbon film on a copper grid for transmission electron microscopy (TEM) characterization. The TEM images were taken on a Hitachi 7700 transmission electron microscope at 100.0 kV. The selected area electron diffraction (SAED) and HRTEM images were taken on a JEM 2100F transmission electron microscope at 300.0 kV. The X-ray diffraction (XRD) patterns of SnSe₂ NSs were acquired on a Rigaku Ultimate-IV X-ray diffractometer. Xray photoelectron spectroscopy (XPS) measurements were carried out on Thermo Scientific ESCALAB 250Xi XPS spectrometer. The thickness of SnSe₂ NSs was qualified by a Bruker Multimode 8 atomic force microscope (AFM). Raman spectrum was measured using home-build microscope with a 532 nm CW laser.

Density Functional Theory (DFT) Calculations. First-principles calculations were performed within the framework of density functional theory (DFT), as implemented in the Vienna *ab initio* simulation package (VASP)². The exchange-correlation effects were treated using the Generalized Gradient Approximation (GGA) functional of Perdew, Burke and Ernzerhof³ within the projector augmented wave

method⁴. The plane-wave basis set with a kinetic energy cutoff of 400 eV was used to expand the wave functions. The convergence thresholds for electronic and ionic relaxations were chosen to be 1.0×10^{-5} eV and 0.01 eV/ Å, respectively. The Brillouin zone was sampled using a Γ centered k-point schemes with a $12 \times 12 \times 8$ grid mesh. DFT-D2 method⁵ was employed to describe the interlayer van der Waals interactions. The electronic structures were calculated using a more accurate one-shot GW (G₀W₀) approach⁶, where the involved total band number was about ten times larger than that of valence bands. The energy cutoff for the response function was set to be 150 eV. The maximally localized Wannier function⁷, as implemented in the wannier90 package⁸ was employed to interpolate the quasi-particle band structures of the G₀W₀ calculations, where p orbitals of Sn and Se atoms were chosen for the initial projections. In order to include the excitonic effects in optical spectra, the Bethe-Salpeter equation (BSE) calculations were carried out on top of the G₀W₀ method with the Tamm-Dancoff approximation⁹.

Femtosecond Transient Absorption Measurement. SnSe₂ NSs dispersed in chloroform were loaded into 1mm quartz cuvette for transient absorption measurement. For femtosecond transient absorption spectroscopy (Time-Tech Spectra, TA100), the fundamental output from Yb:KGW laser (1030 nm, 220 fs Gaussian fit, 100 kHz, Light Conversion Ltd) was separated to two light beam. One was introduced to NOPA (ORPHEUS-N, Light Conversion Ltd) to produce a certain wavelength for pump beam, the other was focused onto a YAG plate to generate white light continuum as probe beam. The pump and probe overlapped on the sample at a small angle less than 10°.

The transmitted probe light from sample was collected by a linear array detector.



SI8. Transient absorption spectra and kinetics on exfoliated SnSe₂ flakes

Fig. S8. (a) TA spectra of a representative exfoliated $SnSe_2$ flakes. (b) TA kinetics at 920nm. Inset: the optical image of measured flake.

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